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# NVMFS5830NL

## Power MOSFET

40 V, 2.3 mΩ, 185 A, Single N-Channel

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- NVMFS5830NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                                                                                                                          |                                                            |                                | Symbol            | Value        | Unit               |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------|--------------------------------|-------------------|--------------|--------------------|
| Drain-to-Source Voltage                                                                                                                                                            |                                                            |                                | $V_{DSS}$         | 40           | V                  |
| Gate-to-Source Voltage                                                                                                                                                             |                                                            |                                | $V_{GS}$          | $\pm 20$     | V                  |
| Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4)                                                                                                                        | Steady State                                               | $T_{mb} = 25^{\circ}\text{C}$  | $I_D$             | 185          | A                  |
|                                                                                                                                                                                    |                                                            | $T_{mb} = 100^{\circ}\text{C}$ |                   | 131          |                    |
| Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3)                                                                                                                                  |                                                            | $T_{mb} = 25^{\circ}\text{C}$  | $P_D$             | 158          | W                  |
|                                                                                                                                                                                    |                                                            | $T_{mb} = 100^{\circ}\text{C}$ |                   | 79           |                    |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)                                                                                                                           | Steady State                                               | $T_A = 25^{\circ}\text{C}$     | $I_D$             | 29           | A                  |
|                                                                                                                                                                                    |                                                            | $T_A = 100^{\circ}\text{C}$    |                   | 20           |                    |
| Power Dissipation $R_{\theta JA}$ (Notes 1 & 3)                                                                                                                                    |                                                            | $T_A = 25^{\circ}\text{C}$     | $P_D$             | 3.8          | W                  |
|                                                                                                                                                                                    |                                                            | $T_A = 100^{\circ}\text{C}$    |                   | 1.9          |                    |
| Pulsed Drain Current                                                                                                                                                               | $T_A = 25^{\circ}\text{C}$ , $t_p = 10\text{ }\mu\text{s}$ |                                | $I_{DM}$          | 1012         | A                  |
| Operating Junction and Storage Temperature                                                                                                                                         |                                                            |                                | $T_J$ , $T_{stg}$ | -55 to + 175 | $^{\circ}\text{C}$ |
| Source Current (Body Diode)                                                                                                                                                        |                                                            |                                | $I_S$             | 185          | A                  |
| Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^{\circ}\text{C}$ , $V_{GS} = 10\text{ V}$ , $I_{L(pk)} = 85\text{ A}$ , $L = 0.1\text{ mH}$ , $R_G = 25\text{ }\Omega$ ) |                                                            |                                | $E_{AS}$          | 361          | mJ                 |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                                                                                                                  |                                                            |                                | $T_L$             | 260          | $^{\circ}\text{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                                    | Symbol          | Value | Unit               |
|--------------------------------------------------------------|-----------------|-------|--------------------|
| Junction-to-Mounting Board (top) – Steady State (Notes 2, 3) | $R_{\Psi J-mb}$ | 1.0   | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 3)                  | $R_{\theta JA}$ | 39    |                    |

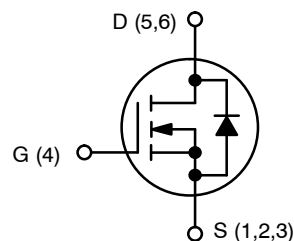
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi ( $\Psi$ ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



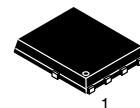
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| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 40 V          | 2.3 mΩ @ 10 V            | 185 A             |
|               | 3.6 mΩ @ 4.5 V           |                   |

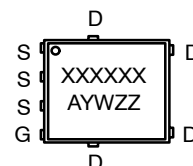


N-CHANNEL MOSFET



DFN5  
(SO-8FL)  
CASE 488AA  
STYLE 1

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVMFS5830NL

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                     |                                  |    |           |                      |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|----------------------------------|----|-----------|----------------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 40                               |    |           | V                    |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |                                                     |                                  | 32 |           | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$         | $T_J = 25\text{ }^\circ\text{C}$ |    | 1         | $\mu\text{A}$        |
|                                                           |                   |                                                     | $T_J = 125^\circ\text{C}$        |    | 100       |                      |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$     |                                  |    | $\pm 100$ | nA                   |

### ON CHARACTERISTICS (Note 5)

|                                            |                  |                                                 |     |     |     |                      |
|--------------------------------------------|------------------|-------------------------------------------------|-----|-----|-----|----------------------|
| Gate Threshold Voltage                     | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 1.4 |     | 2.4 | V                    |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |                                                 |     | 7.2 |     | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance              | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$       |     | 1.7 | 2.3 | $\text{m}\Omega$     |
|                                            |                  | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$      |     | 2.6 | 3.6 |                      |
| Forward Transconductance                   | $g_{FS}$         | $V_{DS} = 5\text{ V}, I_D = 10\text{ A}$        |     | 38  |     | S                    |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                  |  |      |  |             |
|------------------------------|--------------|------------------------------------------------------------------|--|------|--|-------------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$    |  | 5880 |  | $\text{pF}$ |
| Output Capacitance           | $C_{OSS}$    |                                                                  |  | 750  |  |             |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                  |  | 500  |  |             |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 32\text{ V}, I_D = 60\text{ A}$ |  | 58   |  | nC          |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}, I_D = 60\text{ A}$  |  | 113  |  | nC          |
| Threshold Gate Charge        | $Q_{G(TH)}$  | $V_{GS} = 4.5\text{ V}, V_{DS} = 32\text{ V}, I_D = 60\text{ A}$ |  | 5.5  |  | $\text{nC}$ |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                  |  | 19.5 |  |             |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                  |  | 32   |  |             |
| Plateau Voltage              | $V_{GP}$     |                                                                  |  | 3.6  |  |             |

### SWITCHING CHARACTERISTICS (Note 6)

|                     |              |                                                                                           |  |    |  |    |
|---------------------|--------------|-------------------------------------------------------------------------------------------|--|----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 10\text{ A}, R_G = 2.5\text{ }\Omega$ |  | 22 |  | ns |
| Rise Time           | $t_r$        |                                                                                           |  | 32 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                           |  | 40 |  |    |
| Fall Time           | $t_f$        |                                                                                           |  | 27 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                                   |                             |  |      |     |    |
|-------------------------|----------|-----------------------------------------------------------------------------------|-----------------------------|--|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V},$<br>$I_S = 10\text{ A}$                                     | $T_J = 25^{\circ}\text{C}$  |  | 0.74 | 1.0 | V  |
|                         |          |                                                                                   | $T_J = 125^{\circ}\text{C}$ |  | 0.58 |     |    |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$<br>$I_S = 60\text{ A}$ |                             |  | 41   |     | ns |
| Charge Time             | $t_a$    |                                                                                   |                             |  | 19   |     |    |
| Discharge Time          | $t_b$    |                                                                                   |                             |  | 19   |     |    |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                                   |                             |  |      | 33  |    |

5. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

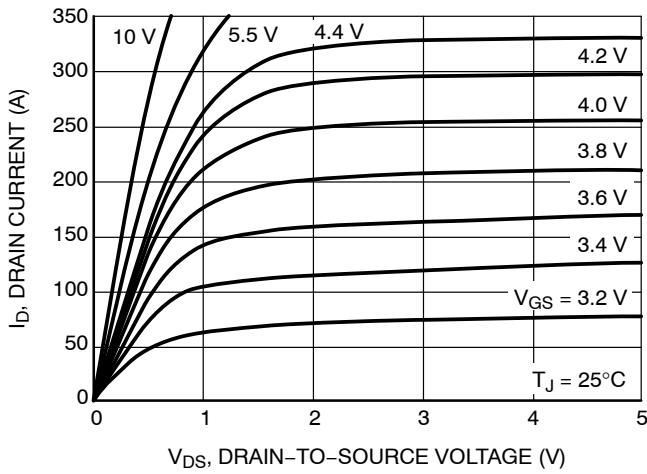


Figure 1. On-Region Characteristics

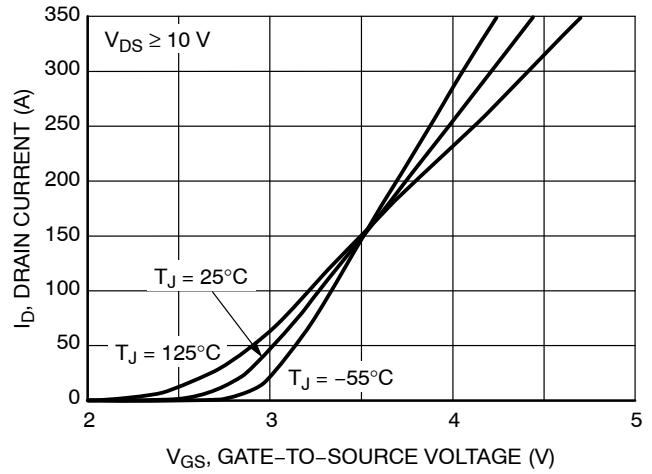


Figure 2. Transfer Characteristics

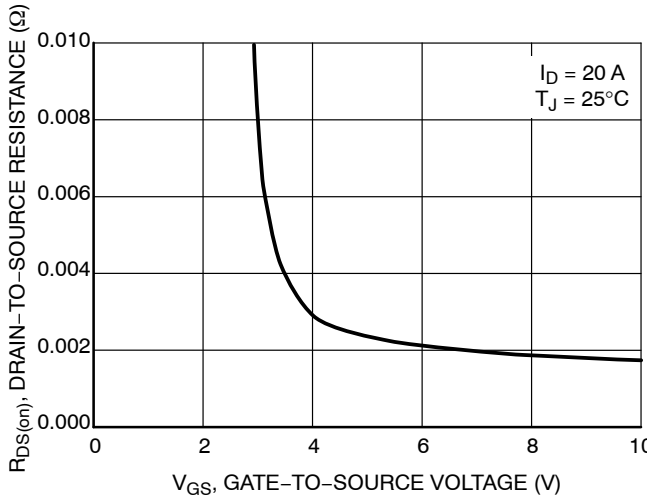


Figure 3. On-Resistance vs. Gate-to-Source Voltage

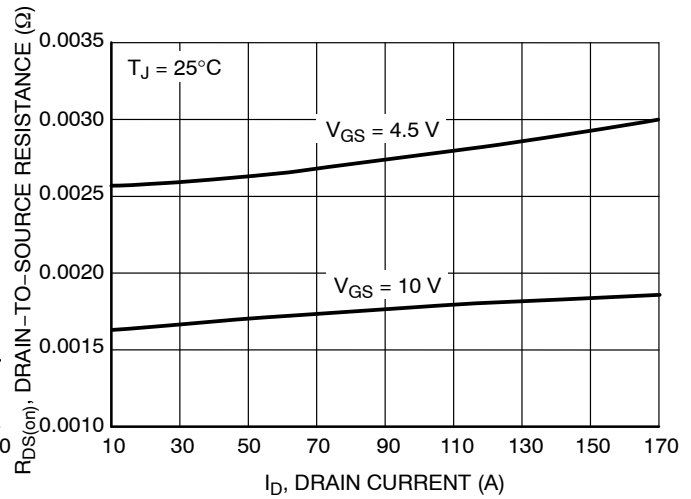


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

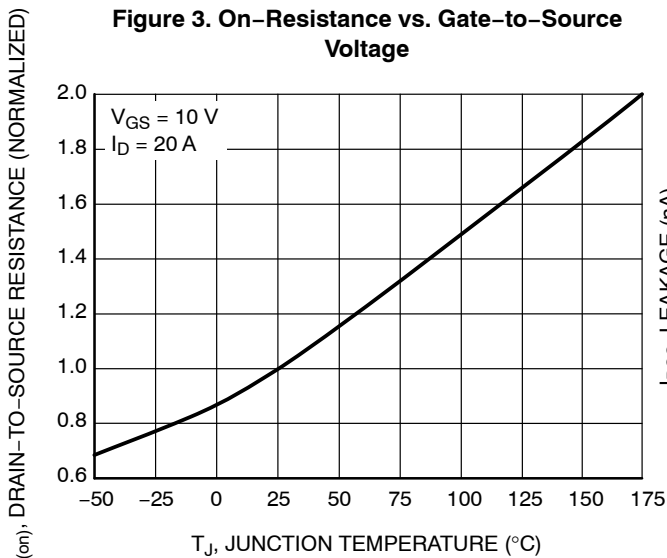


Figure 5. On-Resistance Variation with Temperature

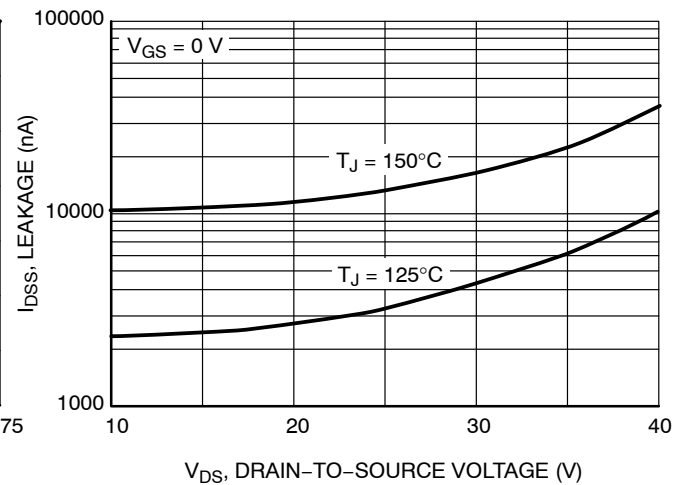


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

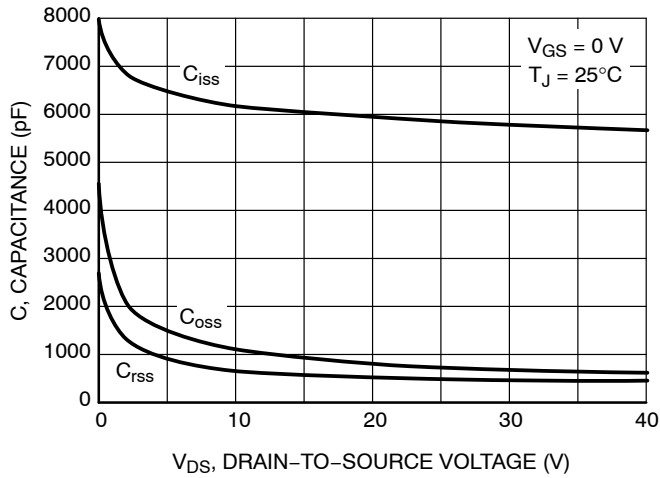


Figure 7. Capacitance Variation

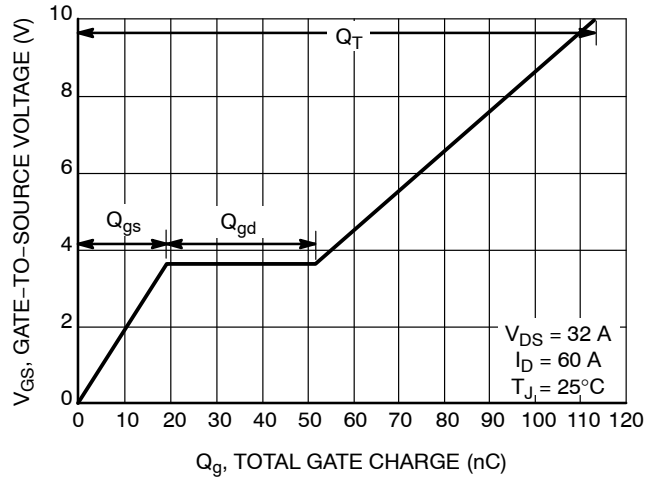


Figure 8. Gate-to-Source Voltage vs. Total Charge

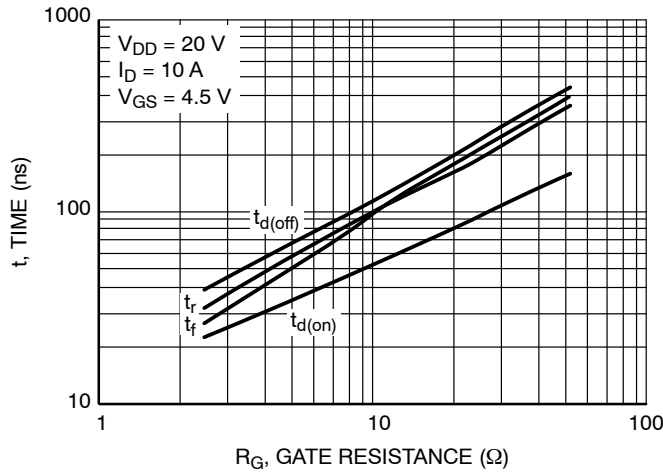


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

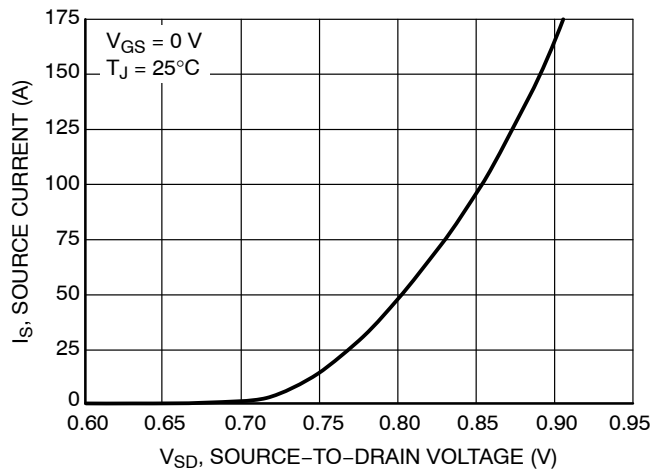


Figure 10. Diode Forward Voltage vs. Current

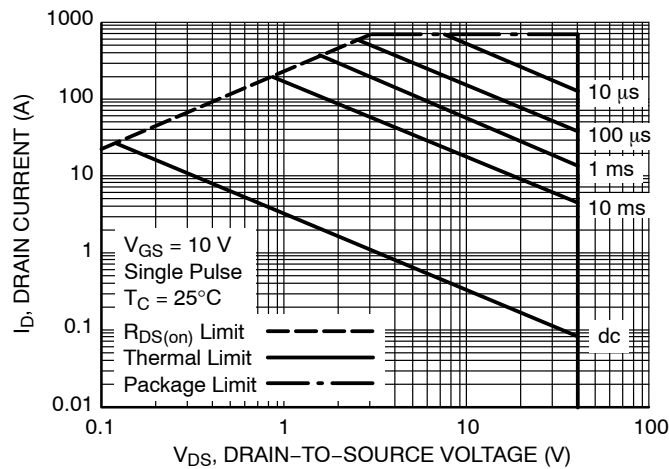


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NVMFS5830NL

## TYPICAL CHARACTERISTICS

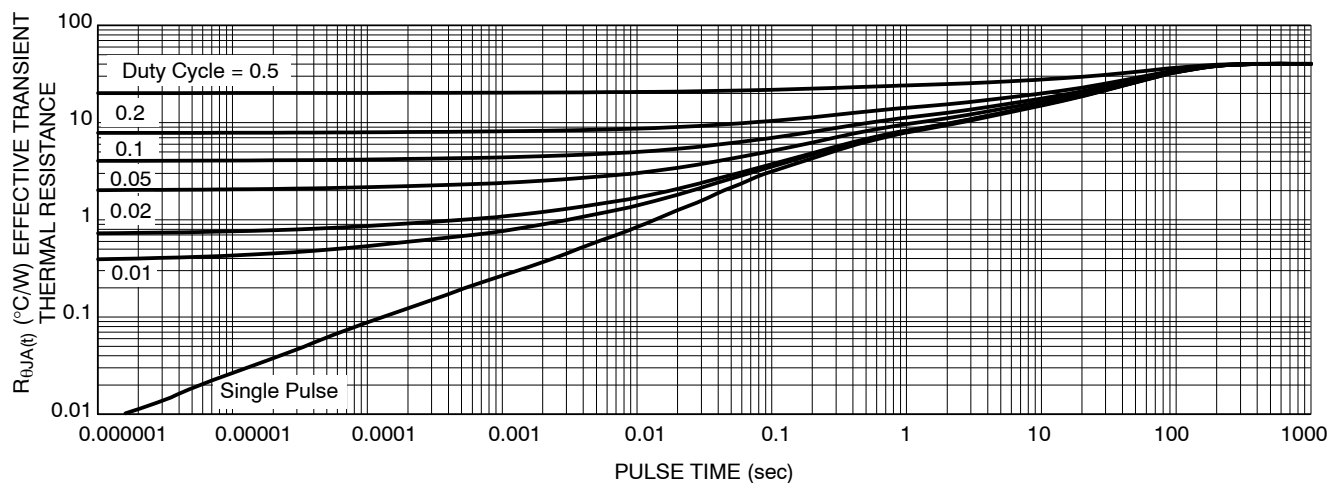


Figure 12. Thermal Response

### DEVICE ORDERING INFORMATION

| Device           | Marking | Package           | Shipping <sup>†</sup> |
|------------------|---------|-------------------|-----------------------|
| NVMFS5830NLT1G   | V5830L  | DFN5<br>(Pb-Free) | 1500 / Tape & Reel    |
| NVMFS5830NLWFT1G | 5830LW  | DFN5<br>(Pb-Free) | 1500 / Tape & Reel    |
| NVMFS5830NLT3G   | V5830L  | DFN5<br>(Pb-Free) | 5000 / Tape & Reel    |
| NVMFS5830NLWFT3G | 5830LW  | DFN5<br>(Pb-Free) | 5000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

